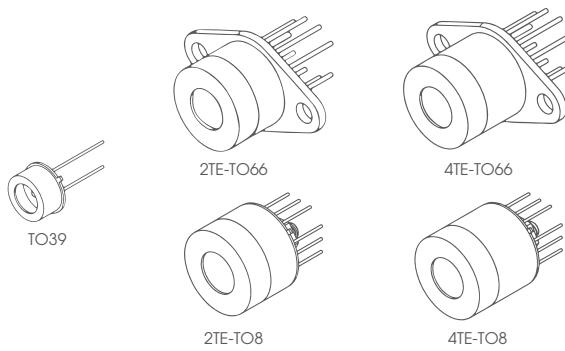


PVI-3 SERIES

HgCdTe room temperature and thermoelectrically cooled photovoltaic optically immersed infrared detectors



FEATURES

- Spectral range: 2.2 to 3.35 μm
- Back-side illuminated
- Unique immersion lens technology applied
- No minimum order quantity required

RELATED PRODUCTS

- **PVA-3-1x1-TO39-NW-90** RoHS-compliant detector (p. 12)
- **PVA-3-d1.2-SMD** RoHS-compliant detector series (p. 14)

APPLICATIONS

- Gas detection, monitoring and analysis: H_2O , HF, CH_4 , C_2H_2 , C_2H_4 , C_2H_6 , NH_3
- Combustion process control
- Green energy
- Medical laser control

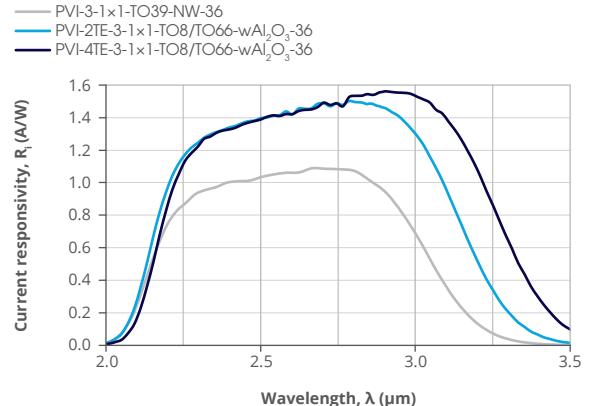
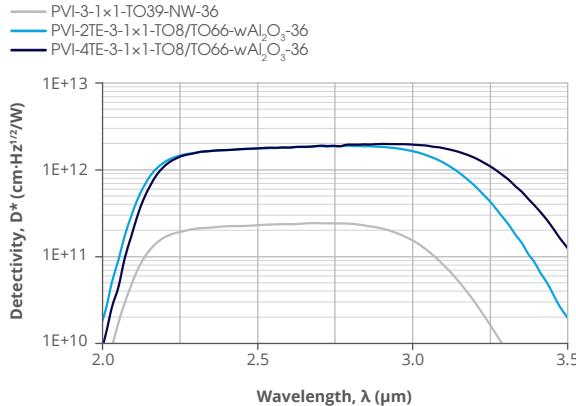
SERIES DESCRIPTION

Detector symbol	Cooling (p. 191)	Temperature sensor (p. 192)	Optical area, A_o , mm \times mm	Optical immersion (p. 188)	Package	Acceptance angle, Φ , deg.	Window (p. 193)
PVI-3-1x1-TO39-NW-36	no	n/a			TO39 (3 pins)		no
PVI-2TE-3-1x1-TO8-wAl ₂ O ₃ -36	2TE $T_{\text{chip}} \approx 230\text{K}$				TO8		
PVI-2TE-3-1x1-TO66-wAl ₂ O ₃ -36		theristor	1x1	hyperhemisphere	TO66	~36	
PVI-4TE-3-1x1-TO8-wAl ₂ O ₃ -36	4TE $T_{\text{chip}} \approx 198\text{K}$				TO8		
PVI-4TE-3-1x1-TO66-wAl ₂ O ₃ -36					TO66		wAl ₂ O ₃ (3 deg. wedged sapphire)

SPECIFICATION ($T_{\text{amb}} = 293\text{ K}$, $V_b = 0\text{ V}$)

Detector symbol	Cut-on wavelength (10%)	Peak wavelength	Specific wavelength	Cut-off wavelength (10%)	Detectivity			Current responsivity			Time constant	Dynamic resistance	
	$\lambda_{\text{cut-on}}$	λ_{peak}	λ_{spec}	$\lambda_{\text{cut-off}}$	$D^*(\lambda_{\text{peak}}, 20\text{kHz})$	$D^*(\lambda_{\text{spec}}, 20\text{kHz})$	$R(\lambda_{\text{peak}})$	$R(\lambda_{\text{spec}})$		τ	R_d		
	μm	μm	μm	μm	cm·Hz ^{1/2} /W	cm·Hz ^{1/2} /W	A/W	A/W	A/W	ns	Ω		
	Typ.	Typ.	Typ.	Typ.	Typ.	Min.	Typ.	Typ.	Min.	Typ.	Typ.	Min.	Typ.
PVI-3-1x1-TO39-NW-36	2.7±0.2		3.15		2.0×10^{11}	8.0×10^{10}	1.5×10^{11}			350	10 000	50 000	
PVI-2TE-3-1x1-TO8-wAl ₂ O ₃ -36													
PVI-2TE-3-1x1-TO66-wAl ₂ O ₃ -36	2.2		3.25		1.5×10^{12}	5.5×10^{11}	1.0×10^{12}	1.4	0.5	280	1 500 000	5 000 000	
PVI-4TE-3-1x1-TO8-wAl ₂ O ₃ -36													
PVI-4TE-3-1x1-TO66-wAl ₂ O ₃ -36	2.8±0.2		3.35		2.0×10^{12}	8.0×10^{11}	1.2×10^{12}					3 000 000	6 000 000

SPECTRAL RESPONSE (Typ., $T_{\text{amb}} = 293 \text{ K}$)



MECHANICAL LAYOUT AND PINOUT

- TO39 (3 pins) package (without the window)
 - Technical drawing (p. 198)
- 2TE-T08 package
 - Technical drawing (p. 204)
- 2TE-T066 package
 - Technical drawing (p. 206)
- 4TE-T08 package
 - Technical drawing (p. 210)
- 4TE-T066 package
 - Technical drawing (p. 212)

RECOMMENDED AMPLIFIERS

Detector symbol	Amplifier type
PVI-3-1x1-T039-NW-36	SIP-T039 series (p. 138)
PVI-2TE-3-1x1-T08-wAl ₂ O ₃ -36	AIP series (p. 126), PIP series (p. 129), MIP series (p. 132), SIP-T08 series (p. 135), FIP series ^{*)} (p. 141)
PVI-4TE-3-1x1-T08-wAl ₂ O ₃ -36	

^{*)} Only for biased detectors

ABSOLUTE MAXIMUM RATINGS

Parameter	Test conditions/remarks	Value	Unit
Ambient operating temperature, T_{amb}	Operation at $T_{\text{amb}} > 30^\circ\text{C}$ may increase the active element temperature and reduce the performance of the detector below specified parameters	-20 to 30	°C
Storage temperature, T_{stg}		-20 to 50	°C
Soldering temperature	Within 5 s or less	≤300	°C
Storage humidity	No dew condensation	10 to 90	%
Maximum incident optical power density	Continuous wave (CW) or single pulses >1 μs duration	2.5	W/cm^2
	Single pulses <1 μs duration	10	kW/cm^2
Maximum bias voltage, $V_{\text{b max}}$		-800	mV
Maximum TEC voltage, $V_{\text{TEC max}}$	2TE	1.3	V
	4TE	8.3	
Maximum TEC current, $I_{\text{TEC max}}$	2TE	1.2	A
	4TE	0.4	

Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. Constant or repeated exposure to absolute maximum rating conditions may affect the quality and reliability of the device.